

MOSFET

650V CoolMOS™ CM8 Power Transistor

The CoolMOS™ 8th generation platform is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. The 650V CoolMOS™ CM8 series is the successor to the 650V CoolMOS™ 7 Family and is enhancing Infineon's WBG offering. It combines the benefits of a fast switching SJ MOSFET with excellent ease of use, e.g. low ringing tendency, implemented fast body diode (CFD) for all products with outstanding robustness against hard commutation and excellent ESD capability. Furthermore, extremely low switching and conduction losses of CM8, make switching applications even more efficient.

Features

- Best in class 650V SJ MOSFET performance
- Suitable for hard and soft switching topologies thanks to an outstanding commutation ruggedness
- Integrated fast body diode and ESD protection
- .XT interconnection technology for best in class thermal performance

Benefits

- Ease of use and fast design-in through low ringing tendency and usage across PFC and PWM stages
- Simplified thermal management due to our advanced die attach technique
- Increased power density solutions enabled by using products with smaller footprint and higher manufacturing quality due state of the art ESD protection
- Suitable for a wide variety of applications and power ranges

Potential applications

- Power supplies and converters
- PFC stages & LLC resonant converters
- High efficiency switching applications
- e.g. Datacenter, AI Server, Telecom Power Supply

Product validation

Fully qualified according to JEDEC for Industrial Applications

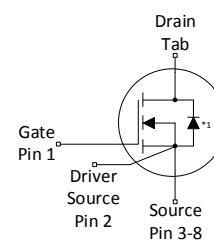
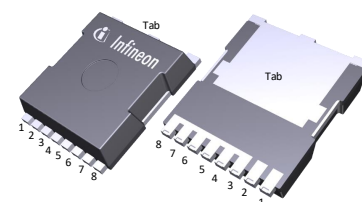
Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key performance parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	25	mΩ
$Q_{g,typ}$	124	nC
$I_{D,pulse}$	359	A
$E_{oss} @ 400V$	14.1	μJ
Body diode di_F/dt	1300	A/μs
ESD class (HBM)	2	

Type / Ordering code	Package	Marking	Related links
IPT65R025CM8	PG-HSOF-8	65R025C8	see Appendix A

TOLL



*1: Internal body diode

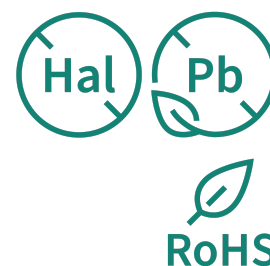




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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	101 63	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	359	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	211	mJ	$I_D=6.0\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	1.06	mJ	
Avalanche current, single pulse	I_{AS}	-	-	6.0	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	120	V/ns	$V_{DS}=0\ldots 400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	543	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	
Extended operating junction temperature	T_j	150	-	175	$^\circ\text{C}$	$\leq 50\text{ h}$ in the application lifetime
Mounting torque	-	-	-	-	Ncm	-
Continuous diode forward current	I_S	-	-	101	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	359	A	
Reverse diode dv/dt ³⁾	dv/dt	-	-	70	V/ns	$V_{DS}=0\ldots 400\text{V}$, $I_{SD}\leq 101\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di_F/dt	-	-	1300	A/ μs	
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.23	K/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	K/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	K/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70μm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave- & reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3.7	4.2	4.7	V	$V_{DS}=V_{GS}, I_D=1.06mA$
Zero gate voltage drain current	I_{DSS}	-	- 151	1.5 -	μA	$V_{DS}=650V, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=650V, V_{GS}=0V, T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	0.1	μA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.021 0.047	0.025 -	Ω	$V_{GS}=10V, I_D=40.0A, T_j=25^\circ\text{C}$ $V_{GS}=10V, I_D=40.0A, T_j=150^\circ\text{C}$
Gate resistance	R_G	-	1	-	Ω	$f=1MHz$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	5910	-	pF	$V_{GS}=0V, V_{DS}=400V, f=250kHz$
Output capacitance	C_{oss}	-	66	-	pF	
Effective output capacitance, energy related ⁴⁾	$C_{o(er)}$	-	176	-	pF	$V_{GS}=0V, V_{DS}=0...400V$
Effective output capacitance, time related ⁵⁾	$C_{o(tr)}$	-	1932	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	28.4	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=21.1A,$ $R_G=1.8\Omega$; see table 9
Rise time	t_r	-	8.6	-	ns	
Turn-off delay time	$t_{d(off)}$	-	121.2	-	ns	
Fall time	t_f	-	5.4	-	ns	

⁴⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

⁵⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	34	-	nC	$V_{DD}=400V$, $I_D=21.1A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	38	-	nC	
Gate charge total	Q_g	-	124	-	nC	
Gate plateau voltage	$V_{plateau}$	-	5.8	-	V	

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=21.1A$, $T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	150	187	ns	$V_R=400V$, $I_F=21.1A$, $di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	1.1	1.66	μC	
Peak reverse recovery current	I_{rrm}	-	15.3	-	A	

4 Electrical characteristics diagrams

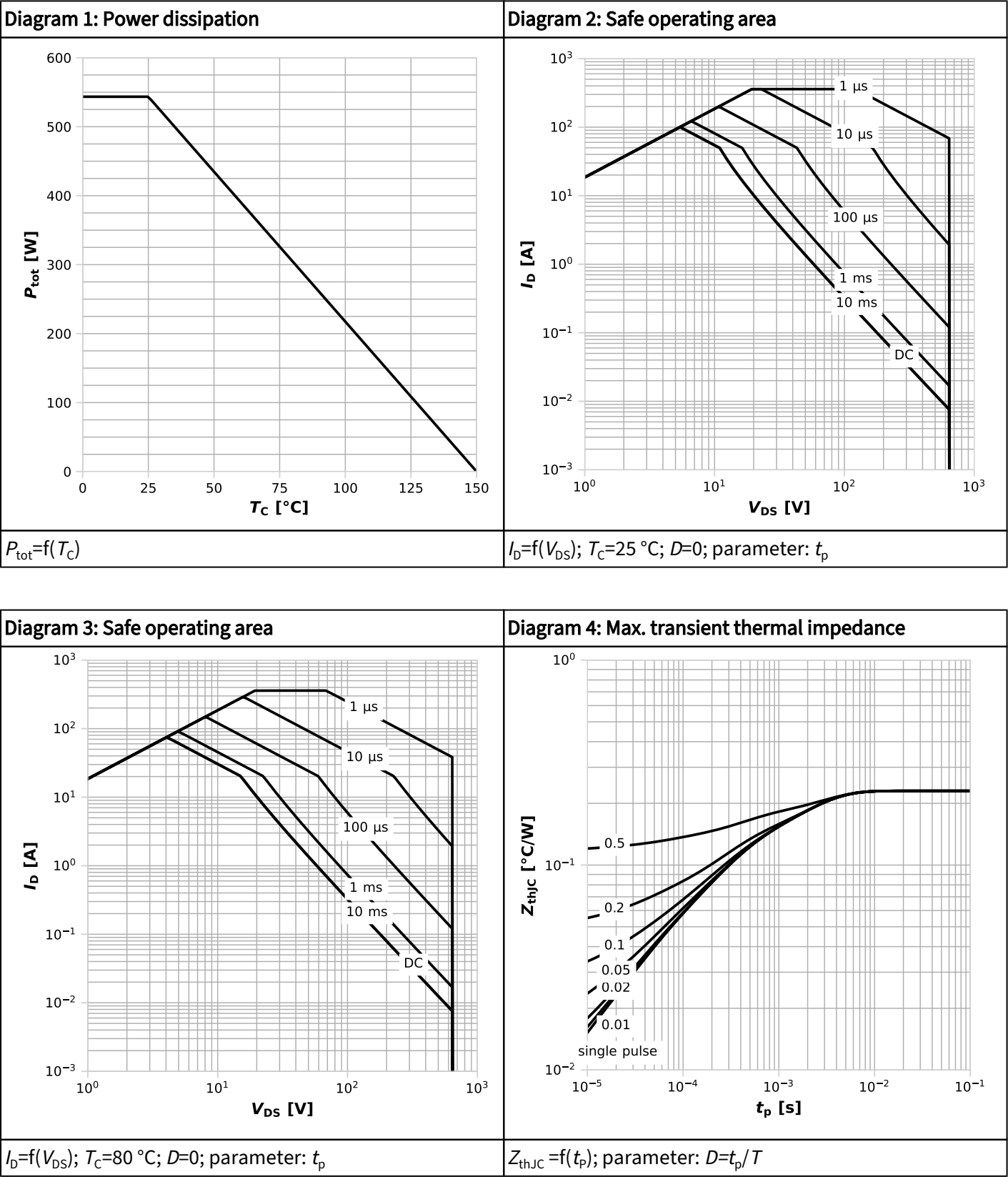
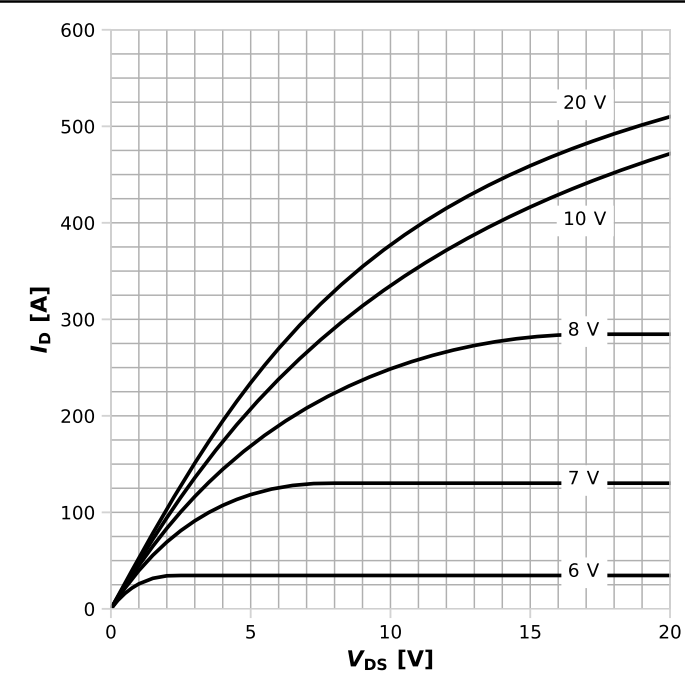
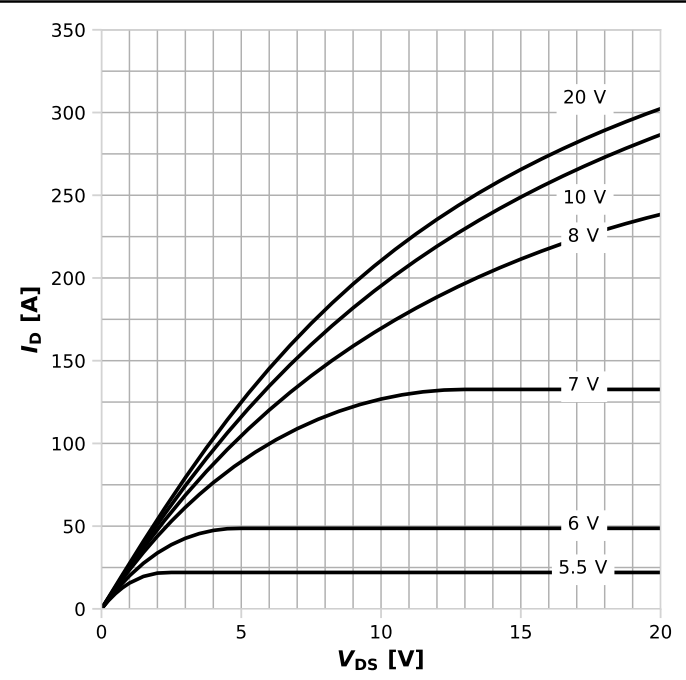


Diagram 5: Typ. output characteristics



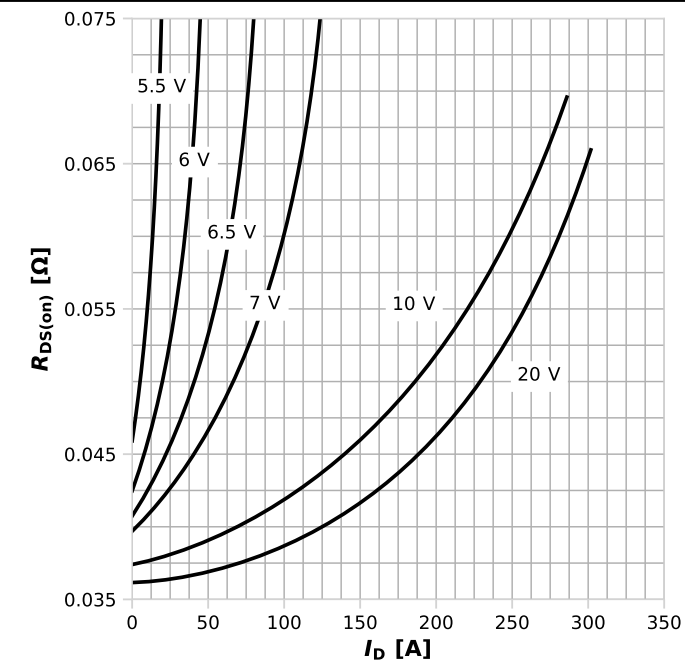
$I_D = f(V_{DS})$; $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



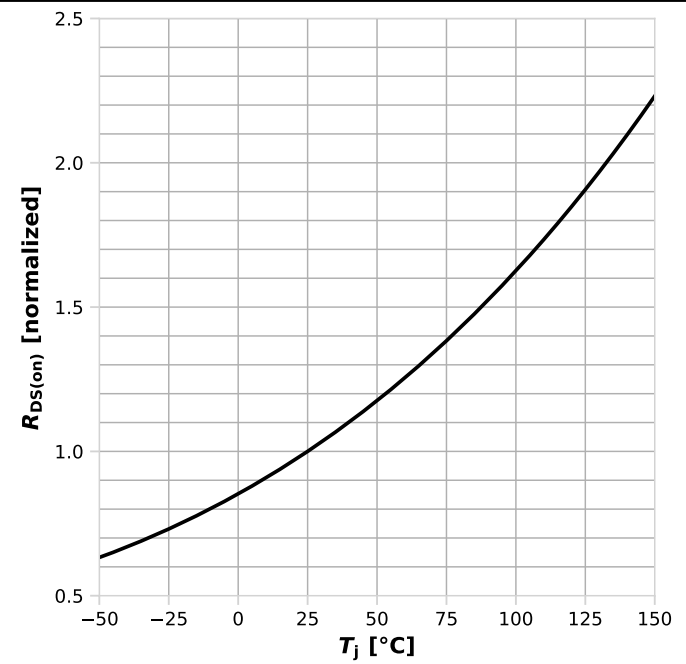
$I_D = f(V_{DS})$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



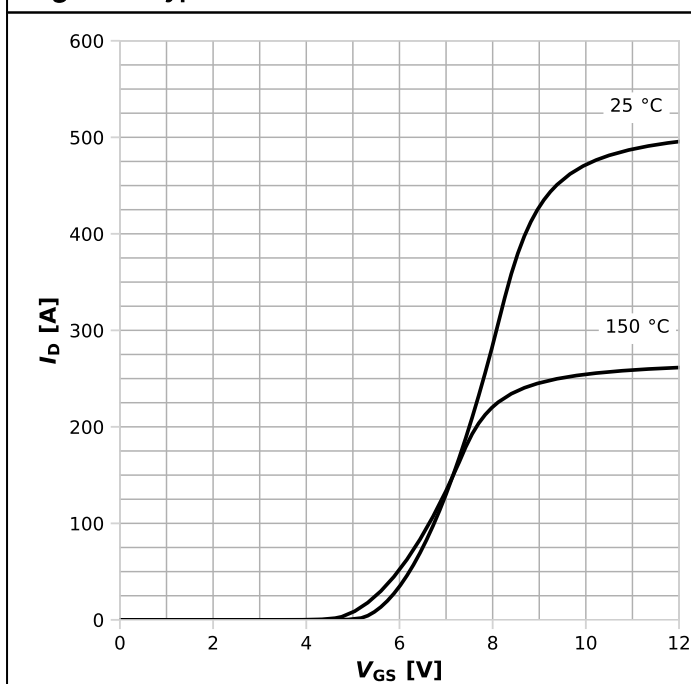
$R_{DS(on)} = f(I_D)$; $T_j = 125\text{ °C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



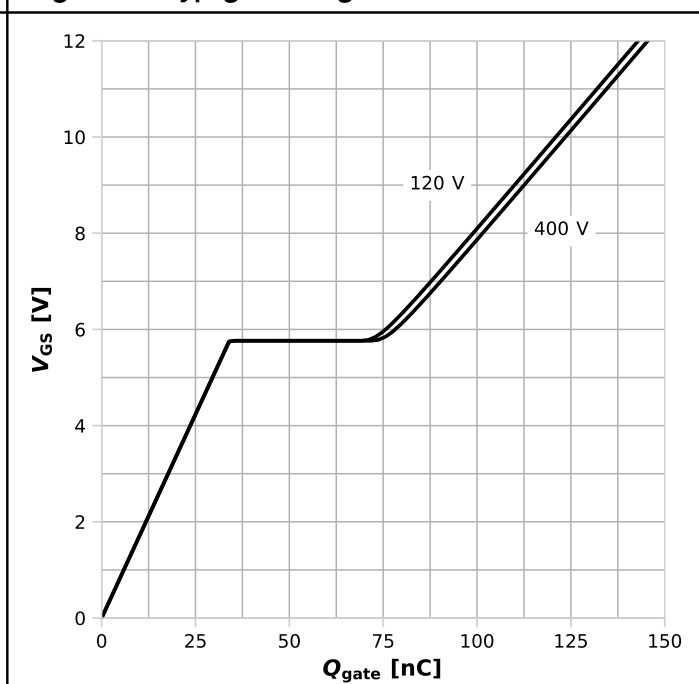
$R_{DS(on)} = f(T_j)$; $I_D = 40.0\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics



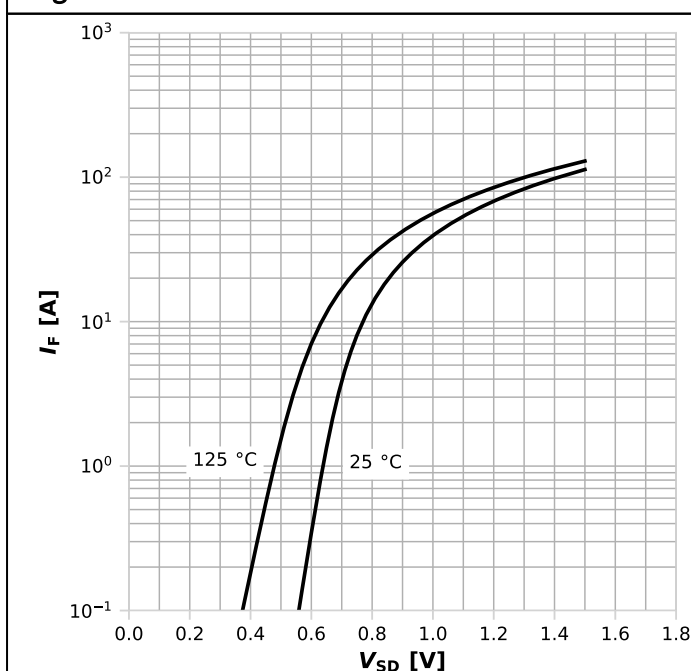
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



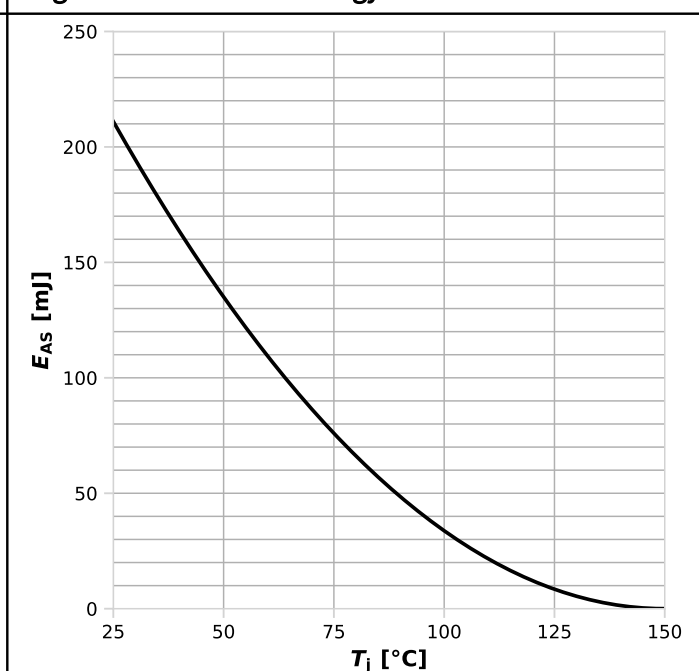
$V_{GS} = f(Q_{gate})$; $I_D = 21.1$ A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



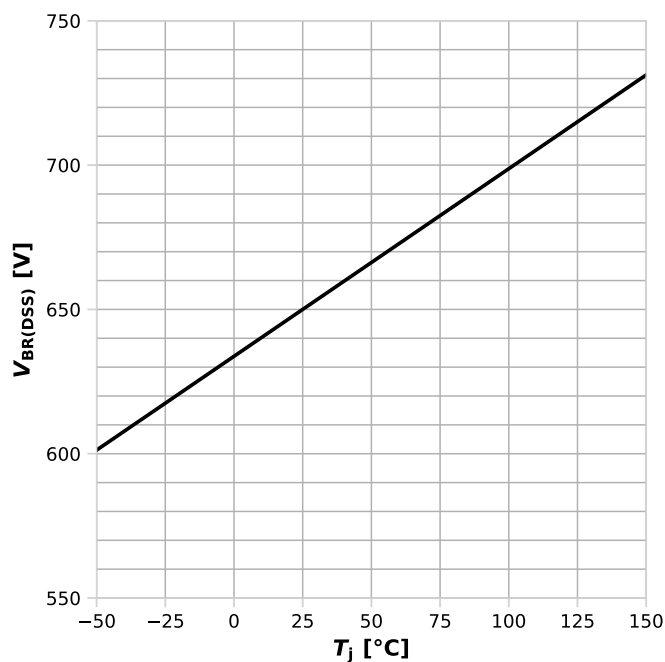
$I_F = f(V_{SD})$; parameter: T_j

Diagram 12: Avalanche energy



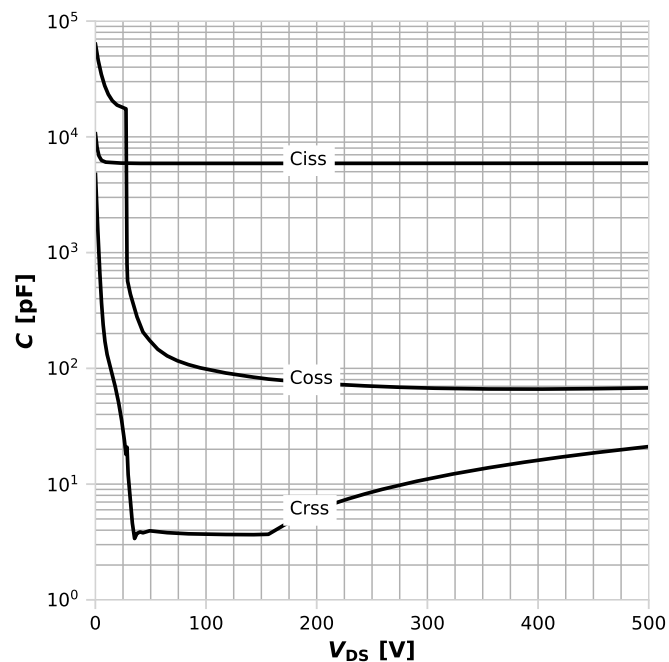
$E_{AS} = f(T_j)$; $I_D = 6.0$ A; $V_{DD} = 50$ V

Diagram 13: Drain-source breakdown voltage



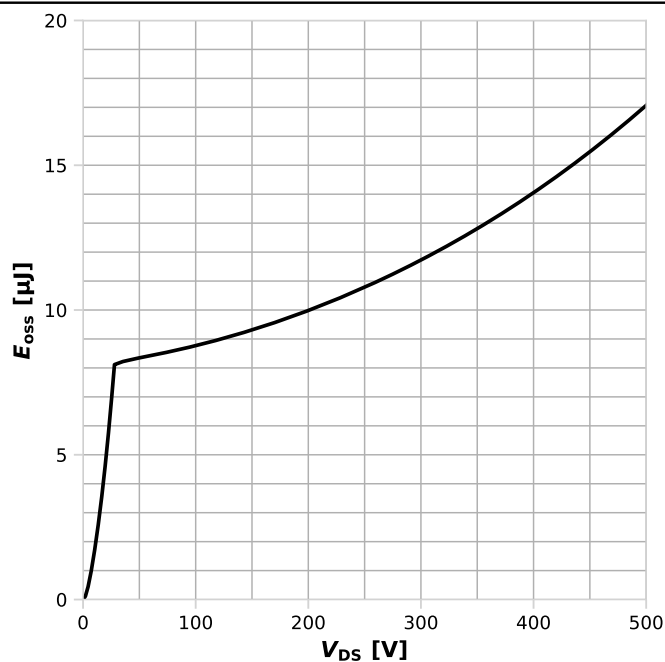
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$

Diagram 14: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$$

Diagram 15: Typ. Coss stored energy



$$E_{oss} = f(V_{DS})$$

5 Test circuits

Table 8 Diode characteristics

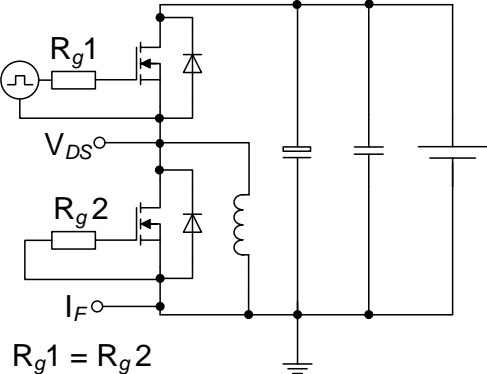
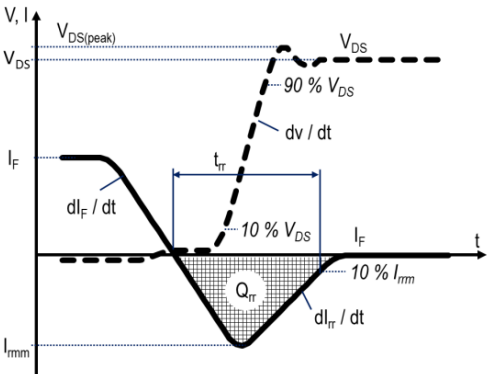
Test circuit for diode characteristics	Diode recovery waveform
 <p>$R_{g1} = R_{g2}$</p>	

Table 9 Switching times (ss)

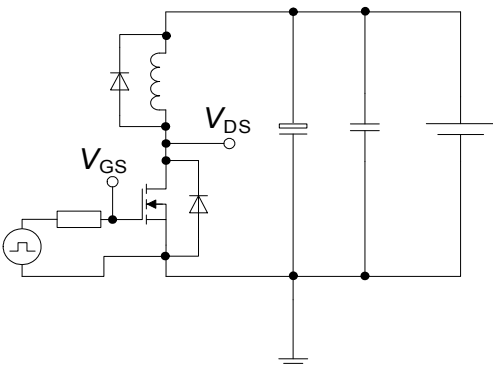
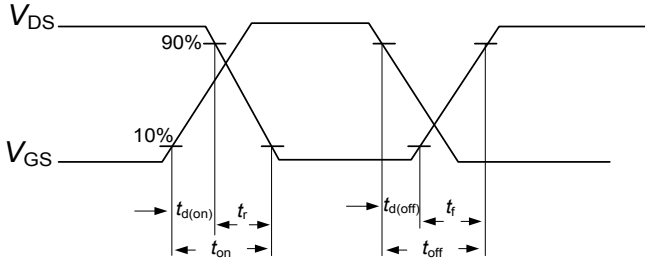
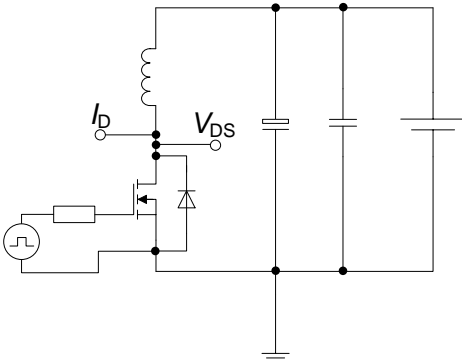
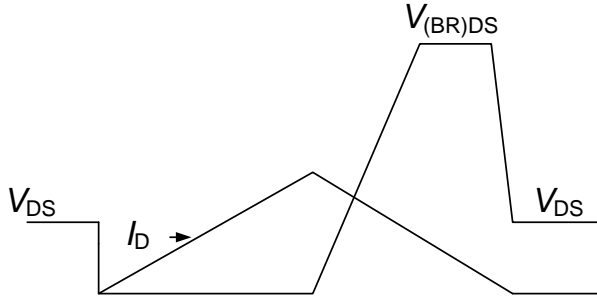
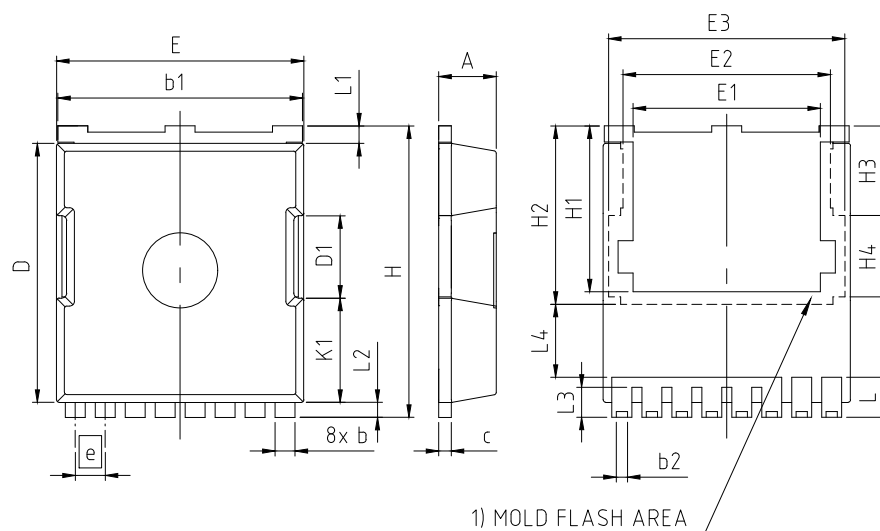
Switching times test circuit for inductive load	Switching times waveform
	

Table 10 Unclamped inductive load (ss)

Unclamped inductive load test circuit	Unclamped inductive waveform
	

6 Package outlines



PACKAGE - GROUP NUMBER: PG-HSOF-8-U02		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D1	3.30	
E	9.70	10.10
E1	7.50	
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.88
H1	6.55	6.95
H2	7.15	
H3	3.59	
H4	3.26	
N	8	
K1	4.18	
L	1.40	1.80
L1	0.50	0.90
L2	0.50	0.70
L3	1.00	1.30
L4	2.62	2.81

1) PARTIALLY COVERED WITH MOLD FLASH

Figure 1 Outline PG-HSOF-8, dimensions in mm

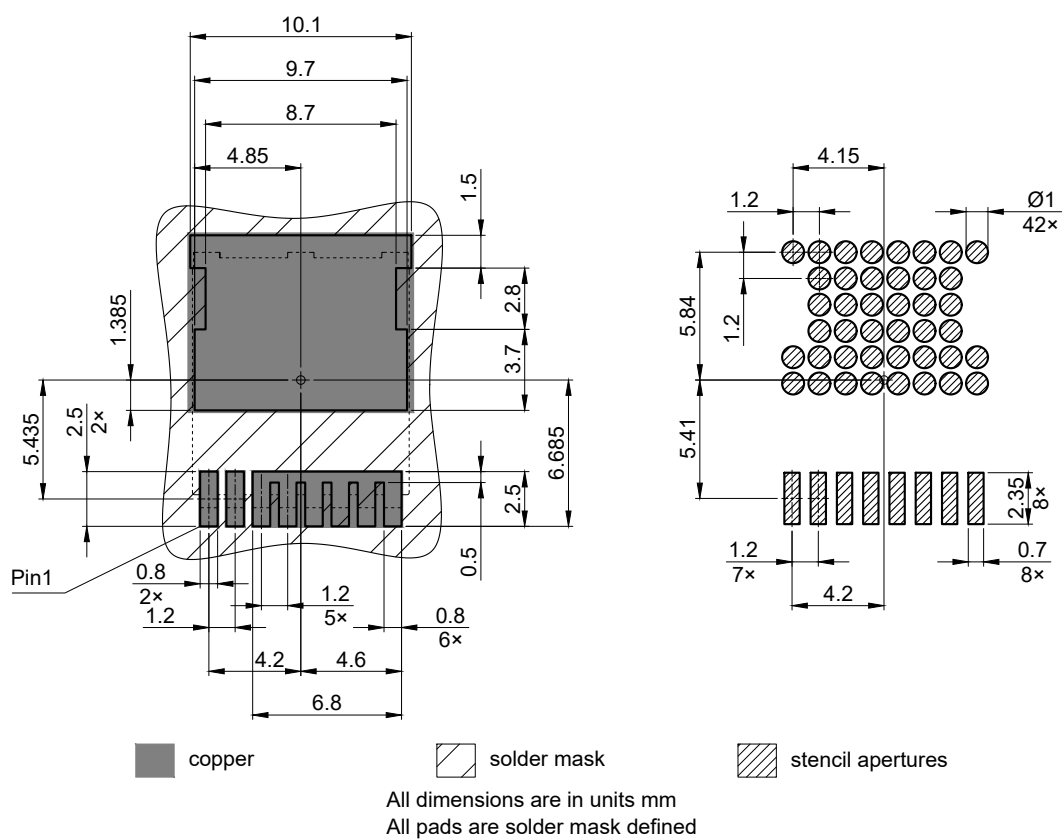
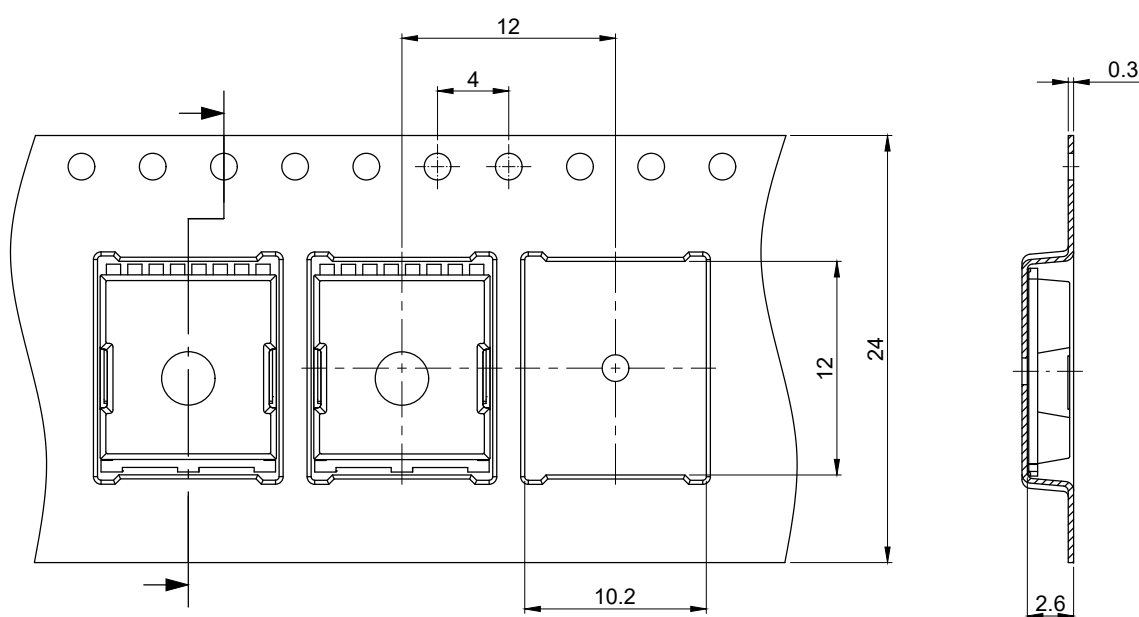


Figure 2 Footprint drawing PG-HSOF-8, dimensions in mm



All dimensions are in units mm


The drawing is in compliance with ISO 128-30, Projection Method 1 []

Figure 3 Packaging variant PG-HSOF-8, dimensions in mm

7 Appendix A

Table 11 **Related links**

- [IFX CoolMOS CM8 Webpage](#)
- [IFX CoolMOS CM8 application note](#)
- [IFX CoolMOS CM8 simulation model](#)
- [IFX Design tools](#)

Revision history

IPT65R025CM8

Revision 2024-12-19, Rev. 2.0

Previous revisions

Revision	Date	Subjects (major changes since last revision)
2.0	2024-12-19	Release of final version

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